ABSTRACT OF THE DISCLOSURE

A photoresist pattern through which a first well forming region and a second well forming region are exposed is formed over a semiconductor substrate, used as the mask to dope the semiconductor substrate with an impurity thereby to form buried n-wells, and further used as the mask to dope the same with an impurity thereby to form shallow p-wells in a self-alignment manner over the buried n-wells. Subsequently, the photoresist pattern is removed. After this, a photoresist pattern through which the outer peripheral region of the first well forming region and a third well forming region are exposed is formed over the major surface of the semiconductor substrate, and used as the mask to dope the semiconductor substrate with an impurity thereby to form shallow p-wells.

This Sheet Has Been Replaced

